

SILICON PRESS-FIT DIODES

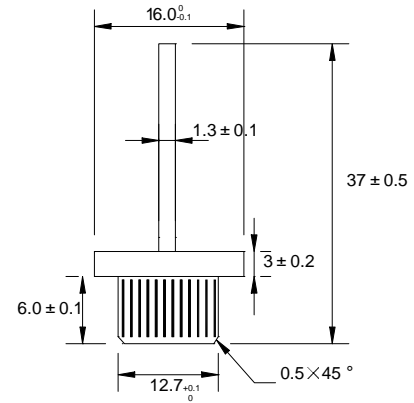
VOLTAGE RANGE: 200 -- 600 V

CURRENT: 50 A

FEATURES

- ◇ Nominal current 50A
- ◇ Repetitive peak reverse voltage 600 V
- ◇ Metal press -fit case with plastic cover

ZQL3



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

		ZQ50A2L3	ZQ50A4L3	ZQ50A6L3	UNITS
Wire to anode		ZQ50A2L3	ZQ50A4L3	ZQ50A6L3	
Wire to cathode		ZQ50K2L3	ZQ50K4L3	ZQ50K6L3	
Repetitive peak reverse voltage	V_{RRM}	200	400	600	V
Surge peak reverse voltage	V_{RSM}	240	480	700	V
Max.average forward rectified current, R-load @ $T_A=55^\circ\text{C}$	$I_{F(AV)}$	50			A
Repetitive peak forward current $f > 15\text{Hz}$ (NOTE1)	I_{FRM}	110			A
Peak forward surge current,50/60 Hz half sine-wave	I_{FSM}	450/500			A
Forward voltage @ $I_F=50\text{A}$	V_F	1.1			V
Leakage current @ $T_j=25^\circ\text{C}$	I_R	100			μA
Rating for fusing $t < 10\text{ms}$	i^2t	800			A^2S
Thermal resistance junction to case	R_{thc}	0.7			K/W
Operating junction temperature	T_j	- 55 --- + 215			$^\circ\text{C}$
Storage temperature range	T_s	- 55 --- + 215			$^\circ\text{C}$

NOTE: Max.case temperature $T_c=150^\circ\text{C}$ -Max.

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FIG.1 – TYPICAL FORWARD CHARACTERISTIC

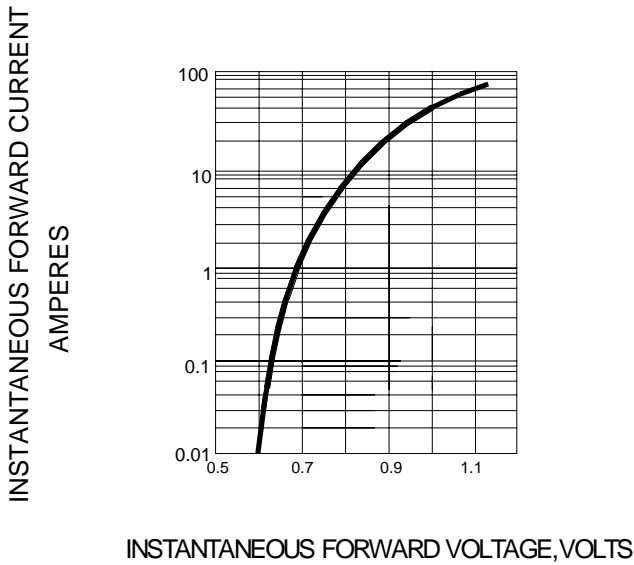


FIG.2 – FORWARD DERATING CURRENT

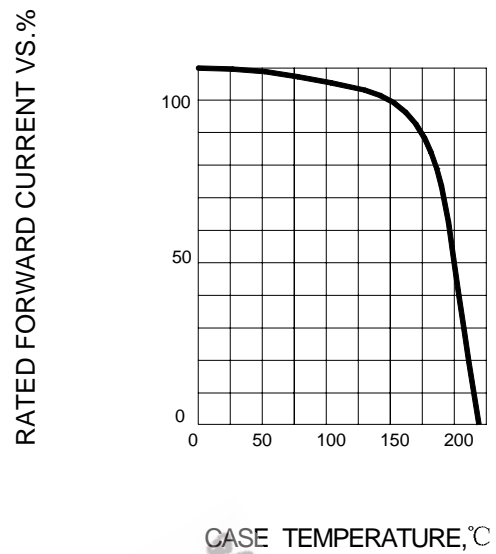


FIG.3 – PEAK FORWARD SURGE CURRENT

